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600V, 6A, 0.75Ω N-Channel Power MOSFET

TSM60N750









Pin Definition:

- 1. Gate 2. Drain
- 3. Source

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	600	V
R _{DS(on)} (max)	0.75	Ω
Q_g	10.8	nC

Features

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

Application

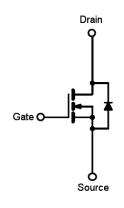
- Power Supply.
- Lighting

Ordering Information

Part No.	Package	Packing
TSM60N750CH C5G	TO-251	75pcs / Tube
TSM60N750CP ROG	TO-252	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Devemeter	Cymphol	Limit	l les is	
Parameter	Symbol	IPAK/DPAK	Unit	
Drain-Source Voltage	V _{DS}	600	٧	
Gate-Source Voltage	V_{GS}	±30	V	
Continuous Drain Current (Note 1) $T_C = 25^{\circ}C$	I _D	6	Α	
Pulsed Drain Current (Note 2)	I _{DM}	18	Α	
Total Power Dissipation @ T _C =25°C	P _{DTOT}	62.5	W	
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	90	mJ	
Single Pulsed Avalanche Current (Note 3)	I _{AS}	1.9	Α	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	- 55 to +150	°C	





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Thermal Performance

Parameter	Symbol	Limit IPAK/DPAK	Unit
Junction to Case Thermal Resistance	R _{eJC}	2	°C/W
Junction to Ambient Thermal Resistance	R _{eJA}	62	°C/W

Electrical Specifications (T_J=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2	3	4	٧
Gate Body Leakage	$V_{GS}=\pm30V,V_{DS}=0V$	I _{GSS}	-		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}	-		1	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 3A$	R _{DS(ON)}	1	0.53	0.75	Ω
Dynamic (Note 5)						
Total Gate Charge	\/ 000\/ L 04	Q_g	1	10.8		
Gate-Source Charge	$V_{DS} = 380V, I_{D} = 6A,$ $V_{GS} = 10V$	Q_{gs}		2.7		nC
Gate-Drain Charge		Q_{gd}	-	3.7		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}	-	554		
Output Capacitance		C _{oss}	-	46		pF
Gate Resistance	f=1MHz, open drain	R_g		2.7		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		17.3		
Turn-On Rise Time	$\begin{aligned} &V_{DD}=380V,\\ &R_{GEN}=25\Omega,\\ &I_{D}=6A,V_{GS}=10V, \end{aligned}$	t _r	-	22		
Turn-Off Delay Time		$t_{d(off)}$	-	28		ns
Turn-Off Fall Time		t _f		22		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S =6A, V _{GS} =0V	V _{SD}	1		1.4	٧
Reverse Recovery Time	V _B =200V, I _S =3A	t _{rr}	-	182		ns
Reverse Recovery Charge	$dI_F/dt=100A/\mu s$	Q_{rr}		1.3		μC

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L=50mH, I_{AS} =1.9A, V_{DD} =50V, R_{G} =25 Ω , Starting T_{J} =25 $^{\circ}$ C
- 4. Pulse test: PW ≤ 300μs, duty cycle ≤ 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

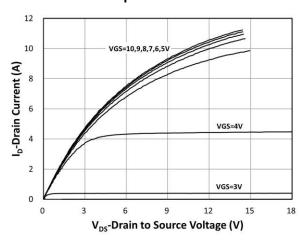




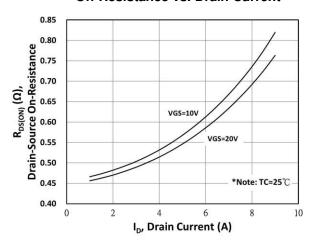
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Electrical Characteristics Curves

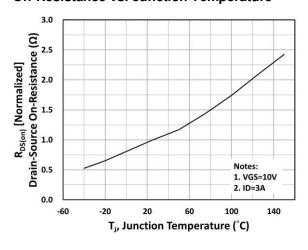
Output Characteristics



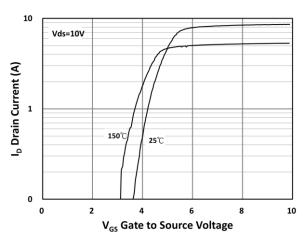
On-Resistance vs. Drain Current



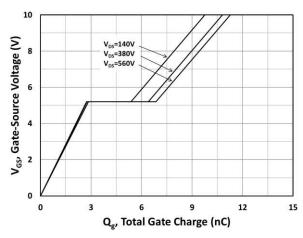
On-Resistance vs. Junction Temperature



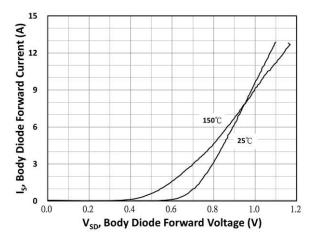
Transfer Characteristics



Gate-Source Voltage vs. Gate Charge



Source-Drain Diode Forward Current vs. Voltage



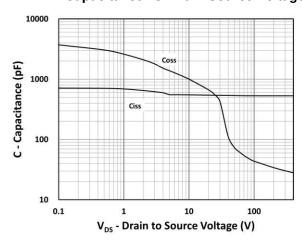


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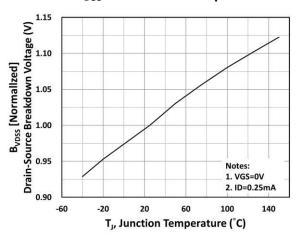


Electrical Characteristics Curves

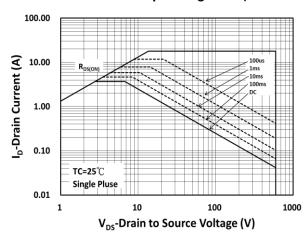
Capacitance vs. Drain-Source Voltage



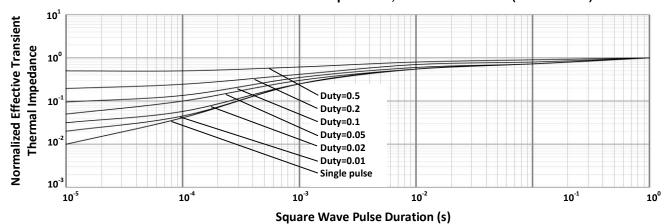
BV_{DSS} vs. Junction Temperature



Maximum Safe Operating Area (DPAK/IPAK)



Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)

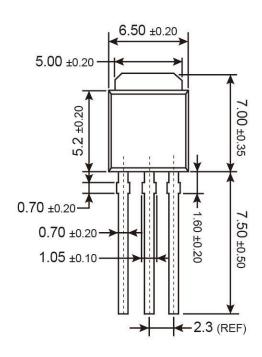


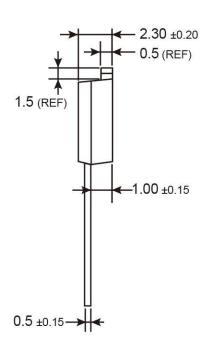




 $600V,\,6A,\,0.75\Omega$ N-Channel Power MOSFET

TO-251 (IPAK) Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

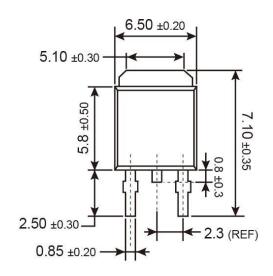
L = Lot Code

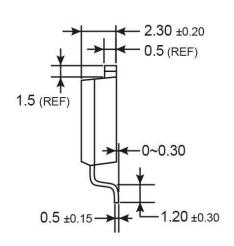


Pb RŏHS

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TO-252 (DPAK) Mechanical Drawing





Unit: Millimeters

Marking Diagram



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